

# 2SC5939

### Silicon NPN epitaxial planar type

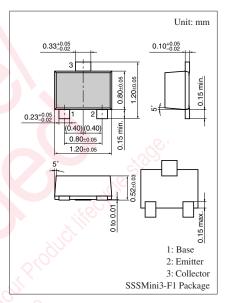
For high-frequency amplification/oscillation/mixing

#### ■ Features

- High transition frequency f<sub>T</sub>
- Small collector output capacitance (Common base, input open circuited) C<sub>ob</sub> and reverse transfer capacitance (Common base) C<sub>rb</sub>
- SSS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

#### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	15	V	
Collector-emitter voltage (Base open)	$V_{CEO}$	10	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	3	V	
Collector current	$I_{C}$	50	mA	
Collector power dissipation	P <sub>C</sub>	100	mW	
Junction temperature	T <sub>j</sub>	125	°C ,	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	



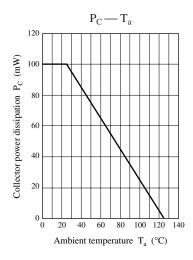
Marking Symbol: 1S

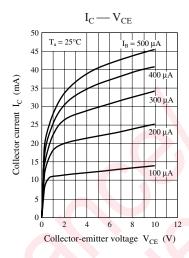
#### ■ Electrical Characteristics $T_a = 25$ °C ± 3°C

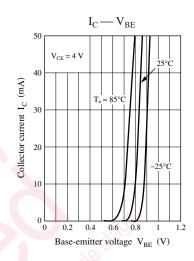
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}, I_B = 0$	10	M		V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10  \mu A, I_C = 0$	3	5		V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 10 \text{ V}, I_{E} = 0$	201		1	μΑ
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 4 \text{ V}, I_{C} = 5 \text{ mA}$	75		400	_
h <sub>FE</sub> ratio	$\Delta h_{FE}$	$V_{CE} = 4 \text{ V}, I_{C} = 100 \mu\text{A}$	0.75		1.6	_
		V <sub>CE</sub> = 4 V, I <sub>C</sub> = 5 mA				
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$			0.5	V
Transition frequency	$f_T$	$V_{CE} = 4 \text{ V}, I_{E} = -5 \text{ mA}, f = 200 \text{ MHz}$	1.4	1.9	2.7	GHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 4 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		1.4		pF
(Common base, input open circuited)		18.02 NICH				
Reverse transfer capacitance	$C_{rb}$	$V_{CB} = 4 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		0.45		pF
(Common base)						
Collector-base parameter	r <sub>bb</sub> ' • C <sub>C</sub>	$V_{CB} = 4 \text{ V}, I_{E} = -5 \text{ mA}, f = 31.9 \text{ MHz}$		11		ps

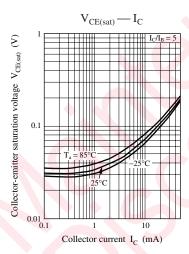
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

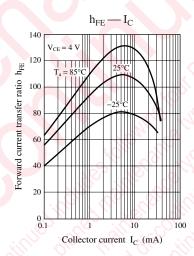
Publication date: April 2004 SJC00306AED 1

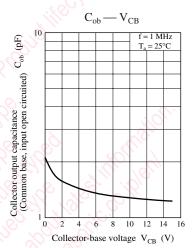












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